

# SGF5N150UF

## General Description

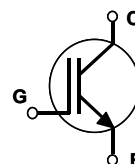
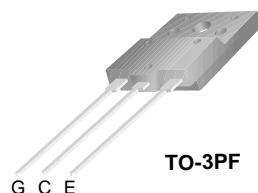
Fairchild's Insulated Gate Bipolar Transistor (IGBT) provides low conduction and switching losses. SGF5N150UF is designed for the Switching Power Supply applications.

## Features

- High Speed Switching
- Low Saturation Voltage :  $V_{CE(sat)} = 4.7 \text{ V @ } I_C = 5 \text{ A}$
- High Input Impedance

## Application

Switching Power Supply - High Input Voltage Off-line Converter



## Absolute Maximum Ratings $T_C = 25^\circ\text{C}$ unless otherwise noted

Symbol	Description	SGF5N150UF	Units
$V_{CES}$	Collector-Emitter Voltage	1500	V
$V_{GES}$	Gate-Emitter Voltage	$\pm 20$	V
$I_C$	Collector Current @ $T_C = 25^\circ\text{C}$	10	A
	Collector Current @ $T_C = 100^\circ\text{C}$	5	A
$I_{CM(1)}$	Pulsed Collector Current	20	A
$P_D$	Maximum Power Dissipation @ $T_C = 25^\circ\text{C}$	62.5	W
	Maximum Power Dissipation @ $T_C = 100^\circ\text{C}$	25	W
$T_J$	Operating Junction Temperature	-55 to +150	$^\circ\text{C}$
$T_{stg}$	Storage Temperature Range	-55 to +150	$^\circ\text{C}$
$T_L$	Maximum Lead Temp. for Soldering Purposes, 1/8" from Case for 5 Seconds	300	$^\circ\text{C}$

### Notes :

(1) Repetitive rating : Pulse width limited by max. junction temperature

## Thermal Characteristics

Symbol	Parameter	Typ.	Max.	Units
$R_{\theta JC}$	Thermal Resistance, Junction-to-Case	--	2.0	$^\circ\text{C/W}$
$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient	--	40	$^\circ\text{C/W}$

## Electrical Characteristics of IGBT T<sub>C</sub> = 25°C unless otherwise noted

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Units
Off Characteristics						
$BV_{CES}$	Collector-Emitter Breakdown Voltage	$V_{GE} = 0V, I_C = 1mA$	1500	--	--	V
$I_{CES}$	Collector Cut-Off Current	$V_{CE} = V_{CES}, V_{GE} = 0V$	--	--	1.0	mA
$I_{GES}$	G-E Leakage Current	$V_{GE} = V_{GES}, V_{CE} = 0V$	--	--	$\pm 100$	nA
On Characteristics						
$V_{GE(th)}$	G-E Threshold Voltage	$I_C = 5mA, V_{CE} = V_{GE}$	2.0	3.0	4.0	V
$V_{CE(sat)}$	Collector to Emitter Saturation Voltage	$I_C = 5A, V_{GE} = 10V$	--	4.7	5.5	V
Dynamic Characteristics						
$C_{ies}$	Input Capacitance	$V_{CE} = 10V, V_{GE} = 0V,$ $f = 1MHz$	--	780	--	pF
$C_{oes}$	Output Capacitance		--	130	--	pF
$C_{res}$	Reverse Transfer Capacitance		--	70	--	pF
Switching Characteristics						
$t_{d(on)}$	Turn-On Delay Time	$V_{CC} = 600V$ $I_C = 5A$ $R_G = 10\Omega$ $V_{GE} = 10V$ Inductive Load $T_C = 25^\circ C$	--	10	--	ns
$t_r$	Rise Time		--	15	--	ns
$t_{d(off)}$	Turn-Off Delay Time		--	30	50	ns
$t_f$	Fall Time		--	70	120	ns
$E_{on}$	Turn-On Switching Loss		--	190	--	uJ
$E_{off}$	Turn-Off Switching Loss	$V_{CE} = 600V, I_C = 5A$ $V_{GE} = 10V$	--	100	--	uJ
$E_{ts}$	Total Switching Loss		--	290	580	uJ
$Q_g$	Total Gate Charge		--	30	45	nC
$Q_{ge}$	Gate-Emitter Charge	$V_{GE} = 10V$	--	3	5	nC
$Q_{gc}$	Gate-Collector Charge		--	15	25	nC

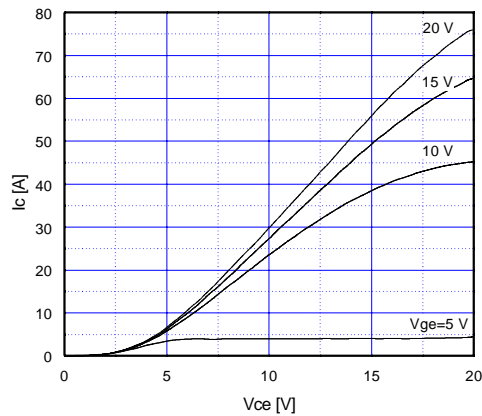


Fig 1. Typical Output Characteristics

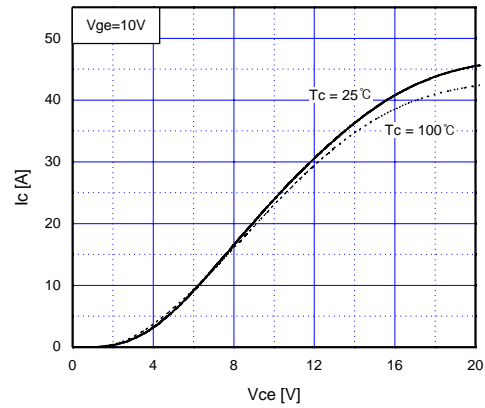


Fig 2. Typical Output Characteristics

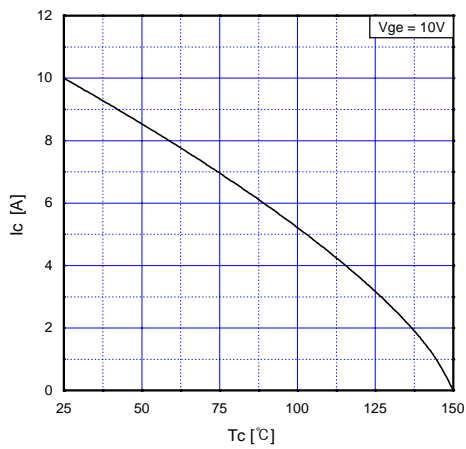


Fig 3. Maximum Collector Current vs. Case Temperature

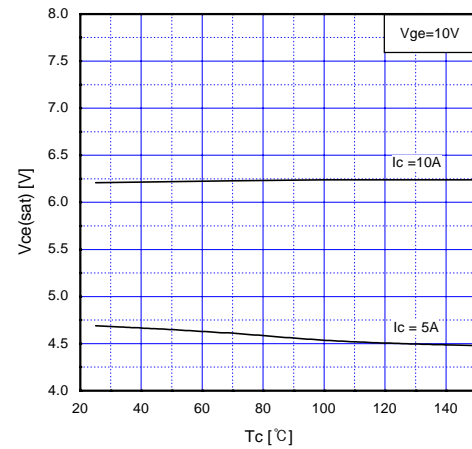


Fig 4. Saturation Voltage vs. Case Temperature

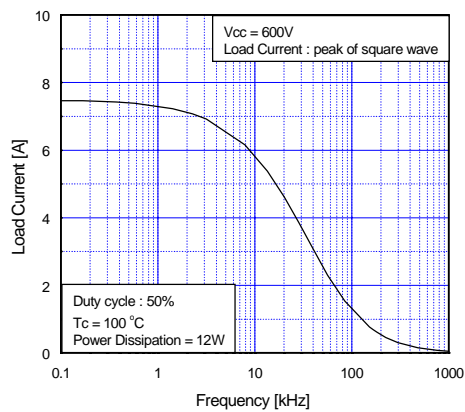


Fig 5. Load Current vs. Frequency

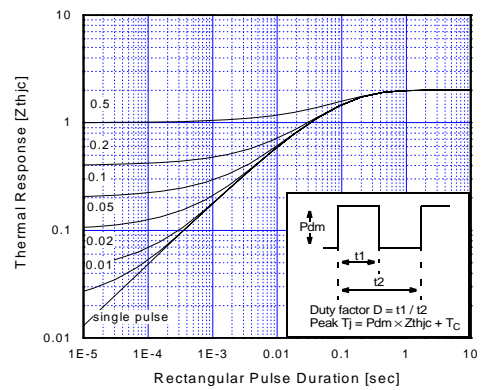


Fig 6. Transient Thermal Impedance of IGBT Junction to Case

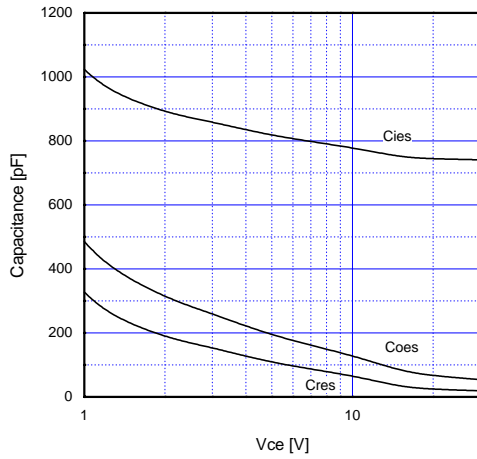


Fig 7. Typical Capacitance vs. Collector to Emitter Voltage

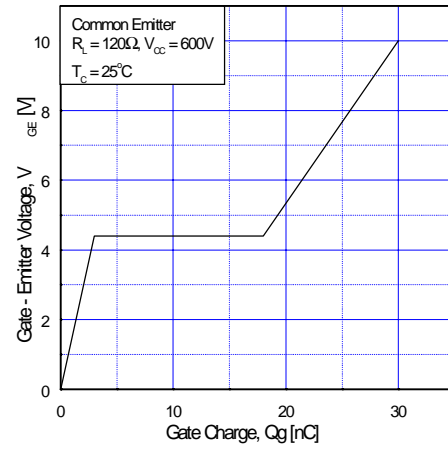


Fig 8. Typical Gate Charge Characteristic

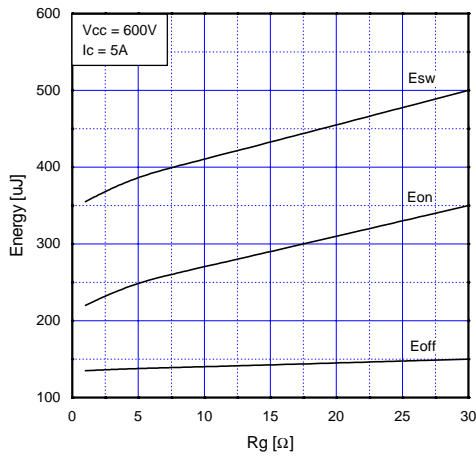


Fig 9. Typical Switching Loss vs. Gate Resistance

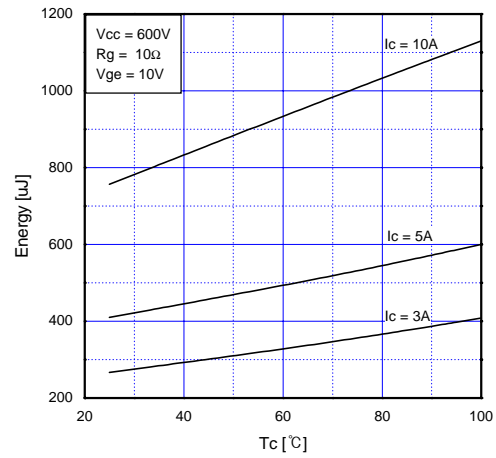


Fig 10. Typical Switching Loss vs. Case Temperature

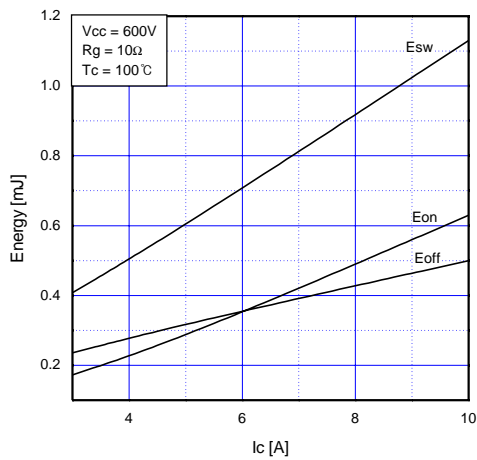


Fig 11. Typical Switching Loss vs. Collector Current

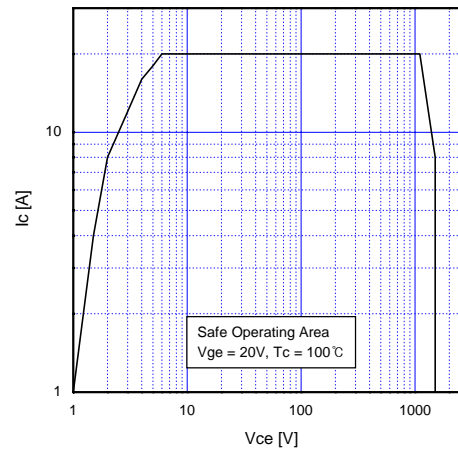
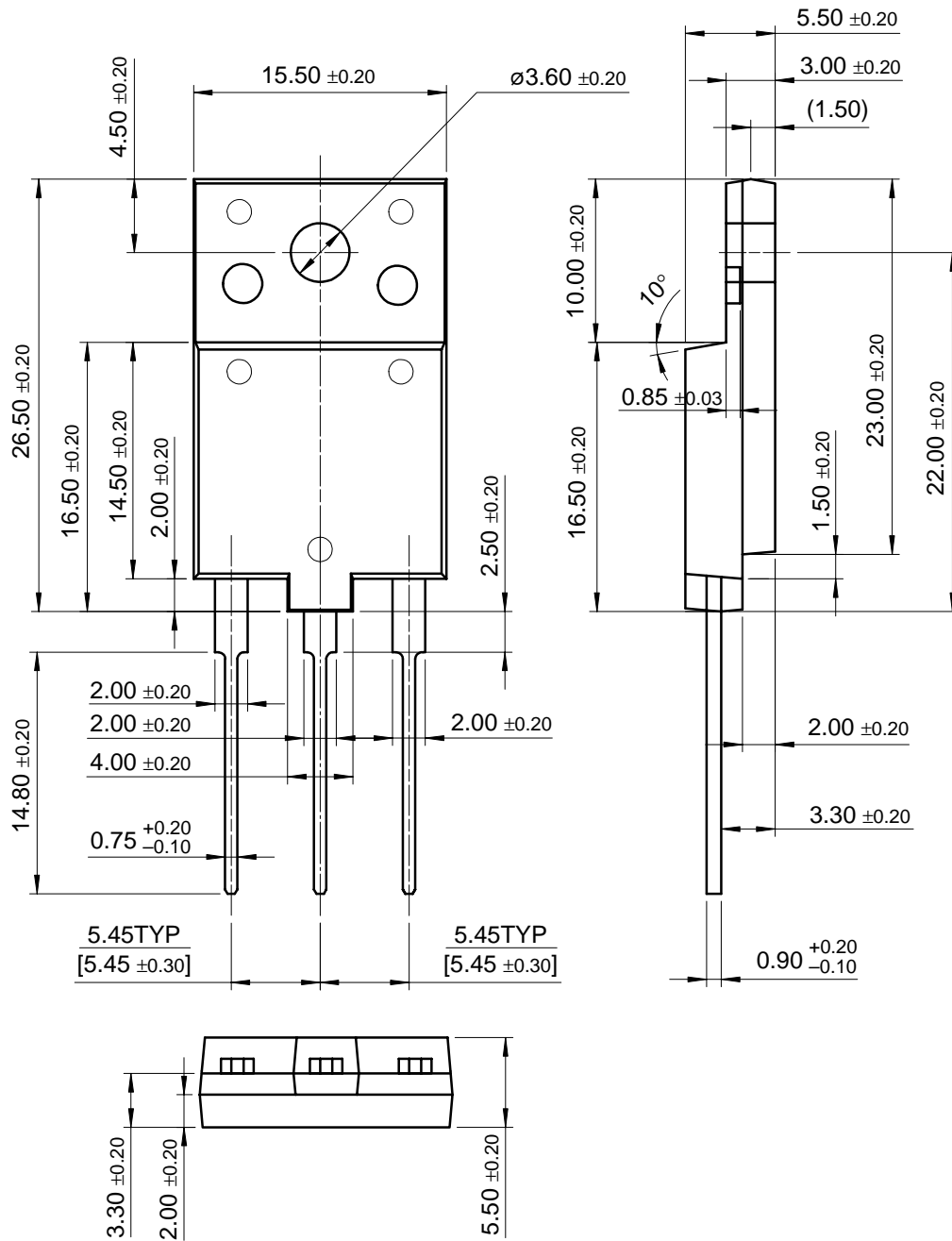


Fig 12. Turn-Off SOA

# Package Dimension

## TO-3PF (FS PKG CODE AG)

SGF5N150UF



Dimensions in Millimeters

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DOMETM	GlobalOptoisolator™	MICROWIRE™	QST™	SyncFET™
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